Undervoltage Sensing Circuit

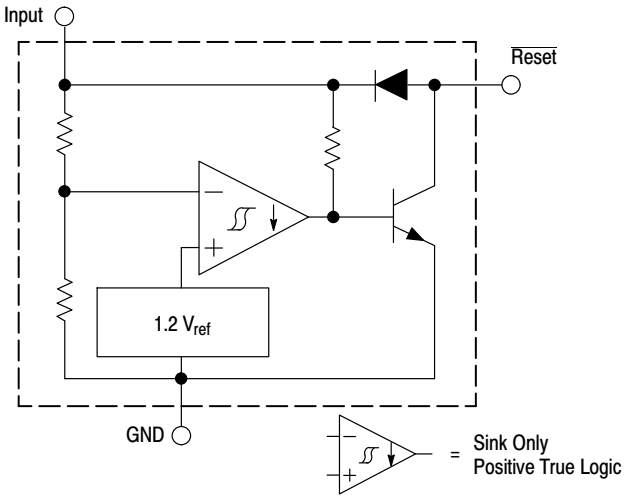
MC34064, MC33064, NCV33064

The MC34064 is an undervoltage sensing circuit specifically designed for use as a reset controller in microprocessor−based systems. It offers the designer an economical solution for low voltage detection with a single external resistor. The MC34064 features a trimmed−in−package bandgap reference, and a comparator with precise thresholds and built-in hysteresis to prevent erratic reset operation. The open collector reset output is capable of sinking in excess of 10 mA, and operation is guaranteed down to 1.0 V input with low standby current. The MC devices are packaged in 3−pin TO-92, micro size TSOP−5, 8−pin SOIC−8 and Micro8 surface mount packages. The NCV device is packaged in SOIC−8 and TO−92.

Applications include direct monitoring of the 5.0 V MPU/logic power supply used in appliance, automotive, consumer and industrial equipment.

Features

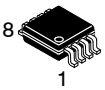
- Trimmed−In−Package Temperature Compensated Reference
- Comparator Threshold of 4.6 V at 25°C
- Precise Comparator Thresholds Guaranteed Over Temperature
- Comparator Hysteresis Prevents Erratic Reset
- Reset Output Capable of Sinking in Excess of 10 mA
- Internal Clamp Diode for Discharging Delay Capacitor
- Guaranteed Reset Operation with 1.0 V Input
- Low Standby Current
- Economical TO−92, TSOP−5, SOIC−8 and Micro8 Surface Mount Packages
- NCV Prefix for Automotive and Other Applications Requiring Site and Control Changes
- These Devices are Pb−Free and are RoHS Compliant



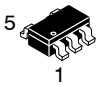
This device contains 21 active transistors.

Figure 1. Representative Block Diagram

SOIC−8
D SUFFIX
CASE 751

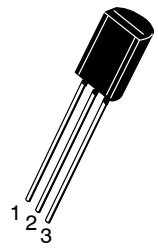


Micro8
DM SUFFIX
CASE 846A

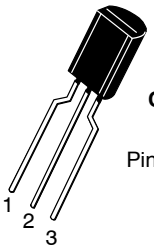


TSOP−5
SN SUFFIX
CASE 483

Pin 1. Ground
2. Input
3. Reset
4. NC
5. NC



STRAIGHT LEAD

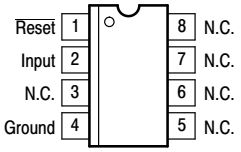


BENT LEAD

TO−92
CASE 29−10

Pin: 1. Reset
2. Input
3. Ground

PIN CONNECTIONS



(Top View)

ORDERING INFORMATION

See detailed ordering and shipping information on page 6 of this data sheet.

NOTE: Some of the devices on this data sheet have been **DISCONTINUED**. Please refer to the table on page 6.

DEVICE MARKING INFORMATION

See general marking information in the device marking section on page 7 of this data sheet.

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MAXIMUM RATINGS

Symbol	Rating	Value	Unit
V_{in}	Power Input Supply Voltage	−1.0 to 10	V
V_O	$\overline{\text{Reset}}$ Output Voltage	10	V
I_{Sink}	$\overline{\text{Reset}}$ Output Sink Current (Note 2)	Internally Limited	mA
I_F	Clamp Diode Forward Current, Reset to Input Pin (Note 2)	100	mA
	Power Dissipation and Thermal Characteristics		
	P Suffix, Plastic Package		
P_D	Maximum Power Dissipation @ T_A = 25°C	625	mW
$R_{\theta JA}$	Thermal Resistance, Junction−to−Air	200	°C/W
	D Suffix, Plastic Package		
P_D	Maximum Power Dissipation @ T_A = 25°C	625	mW
$R_{\theta JA}$	Thermal Resistance, Junction−to−Air	200	°C/W
	DM Suffix, Plastic Package		
P_D	Maximum Power Dissipation @ T_A = 25°C	520	mW
$R_{\theta JA}$	Thermal Resistance, Junction−to−Air	240	°C/W
T_J	Operating Junction Temperature	+150	°C
T_A	Operating Ambient Temperature		°C
	MC34064	0 to +70	
	MC33064	−40 to +85	
	NCV33064	−40 to +125	
T_{stg}	Storage Temperature Range	−65 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. ESD data available upon request.

ELECTRICAL CHARACTERISTICS (For typical values T_A = 25°C, for min/max values T_A is the operating ambient temperature range that applies [Notes 3 and 4] unless otherwise noted.)

Symbol	Characteristics	Min	Typ	Max	Unit
COMPARATOR					
	Threshold Voltage				V
V_{IH}	High State Output (V_{in} Increasing)	4.5	4.61	4.7	
V_{IL}	Low State Output (V_{in} Decreasing)	4.5	4.59	4.7	
V_H	Hysteresis	0.01	0.02	0.05	
$\overline{\text{RESET}}$ OUTPUT					
V_{OL}	Output Sink Saturation				V
	(V_{in} = 4.0 V, I_{Sink} = 8.0 mA)	–	0.46	1.0	
	(V_{in} = 4.0 V, I_{Sink} = 2.0 mA)	–	0.15	0.4	
	(V_{in} = 1.0 V, I_{Sink} = 0.1 mA)	–	–	0.1	
I_{Sink}	Output Sink Current (V_{in}, $\overline{\text{Reset}}$ = 4.0 V)	10	27	60	mA
I_{OH}	Output Off-State Leakage (V_{in}, $\overline{\text{Reset}}$ = 5.0 V)	–	0.02	0.5	μA
V_F	Clamp Diode Forward Voltage, Reset to Input Pin (I_F = 10 mA)	0.6	0.9	1.2	V
TOTAL DEVICE					
V_{in}	Operating Input Voltage Range	1.0 to 6.5	–	–	V
I_{in}	Quiescent Input Current (V_{in} = 5.0 V)	–	390	500	μA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Maximum package power dissipation limits must be observed.
3. Low duty cycle pulse techniques are used during test to maintain junction temperature as close to ambient as possible.
4. T_{low} = 0°C for MC34064, −40°C for MC33064, −40°C for NCV33064; T_{high} = +70°C for MC34064, +85°C for MC33064, +125°C for NCV33064
5. NCV prefix is for automotive and other applications requiring site and change control.

TYPICAL CHARACTERISTICS

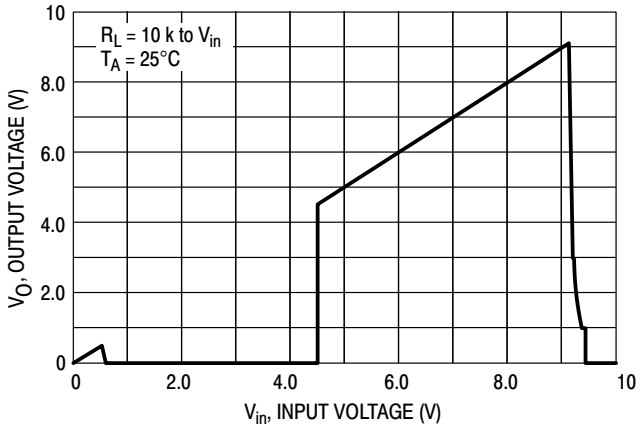


Figure 2. $\overline{\text{Reset}}$ Output Voltage versus Input Voltage

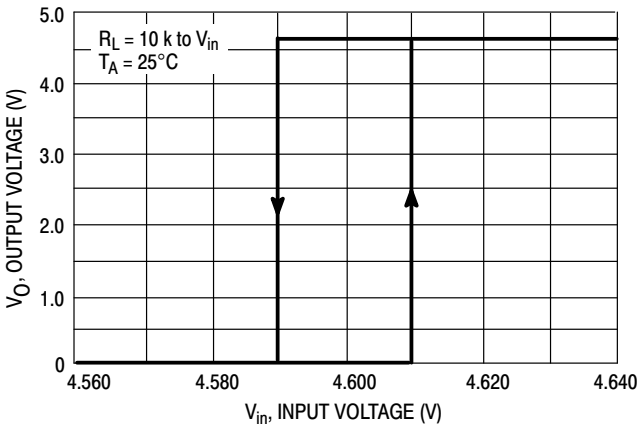


Figure 3. $\overline{\text{Reset}}$ Output Voltage versus Input Voltage

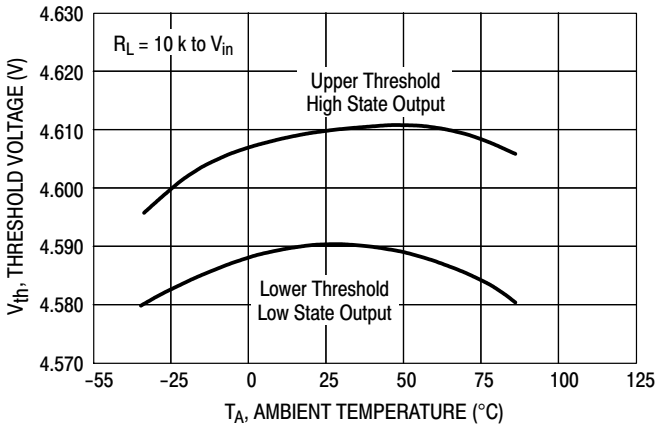


Figure 4. Comparator Threshold Voltage versus Temperature

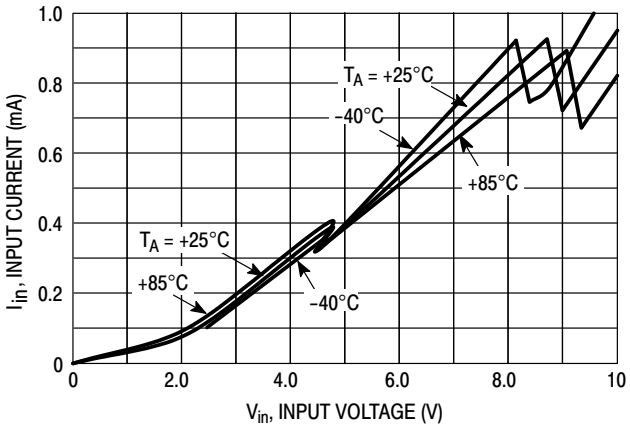


Figure 5. Input Current versus Input Voltage

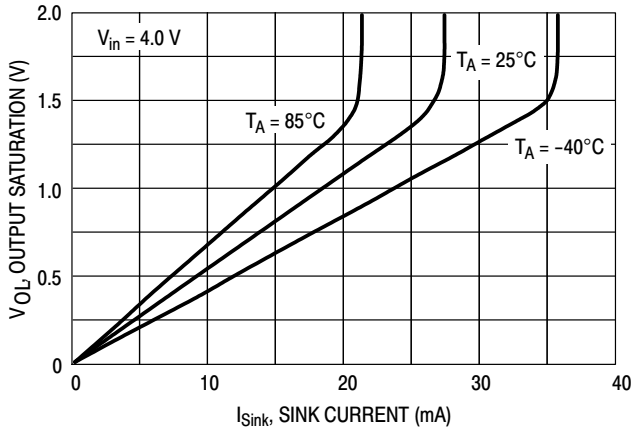


Figure 6. $\overline{\text{Reset}}$ Output Saturation versus Sink Current

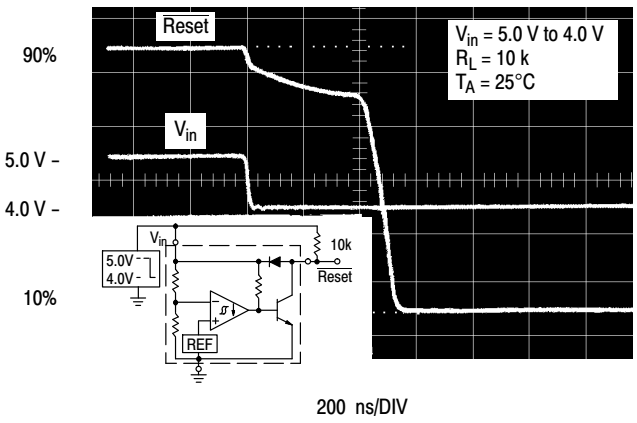


Figure 7. $\overline{\text{Reset}}$ Delay Time

TYPICAL CHARACTERISTICS

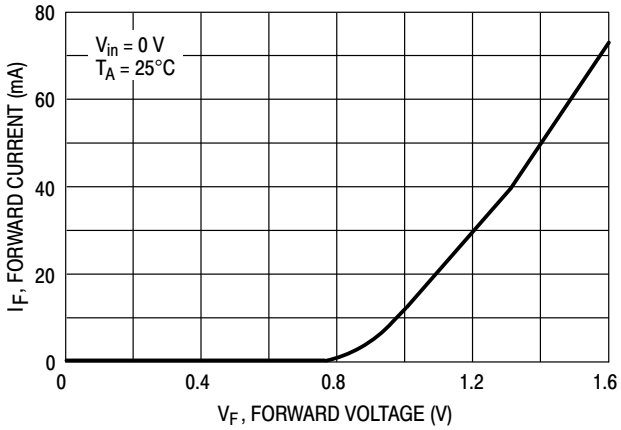


Figure 8. Clamp Diode Forward Current versus Voltage

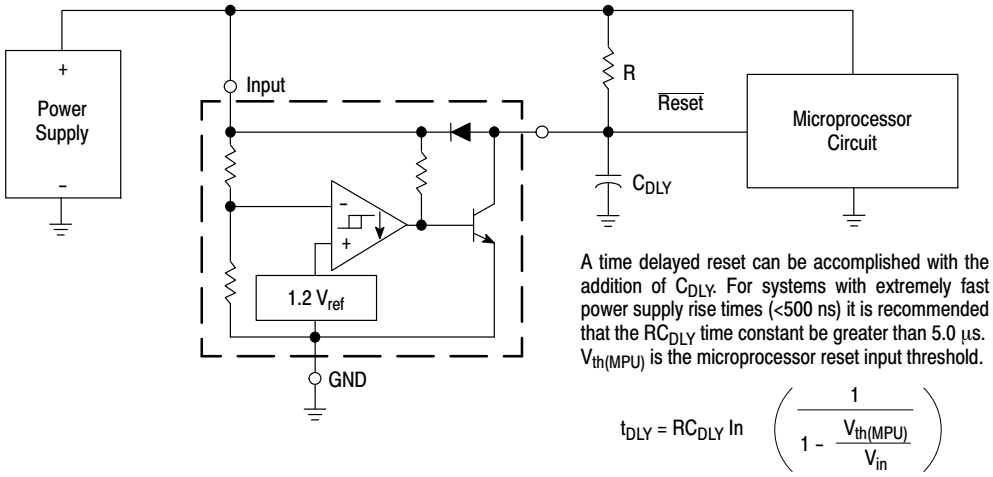
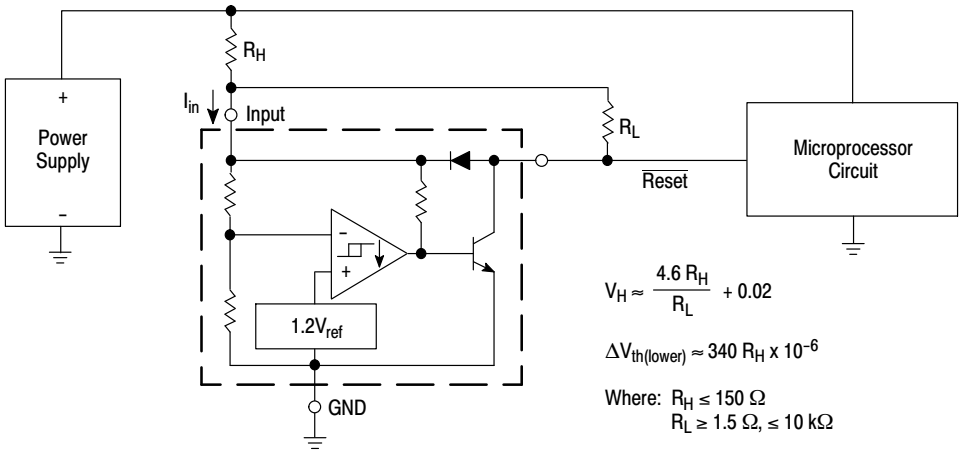


Figure 9. Low Voltage Microprocessor Reset



TEST DATA

V_H (mV)	ΔV_{th} (mV)	R_H (Ω)	R_L (kΩ)
20	0	0	0
51	3.4	10	1.5
40	6.8	20	4.7
81	6.8	20	1.5
71	10	30	2.7
112	10	30	1.5
100	16	47	2.7
164	16	47	1.5
190	34	100	2.7
327	34	100	1.5
276	51	150	2.7
480	51	150	1.5

Comparator hysteresis can be increased with the addition of resistor R_H. The hysteresis equation has been simplified and does not account for the change of input current I_{in} as V_{CC} crosses the comparator threshold (Figure 4). An increase of the lower threshold $\Delta V_{th(lower)}$ will be observed due to I_{in} which is typically 340 μA at 4.59 V. The equations are accurate to ±10% with R_H less than 150 Ω and R_L between 1.5 kΩ and 10 kΩ.

Figure 10. Low Voltage Microprocessor Reset with Additional Hysteresis

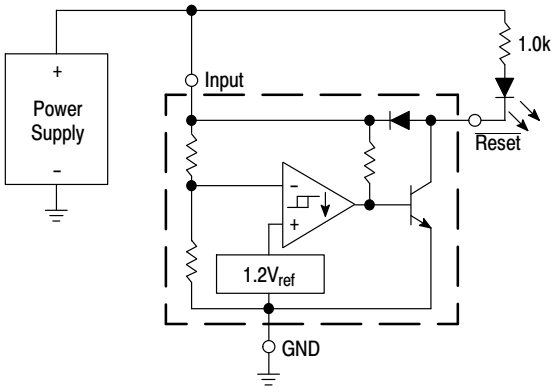


Figure 11. Voltage Monitor

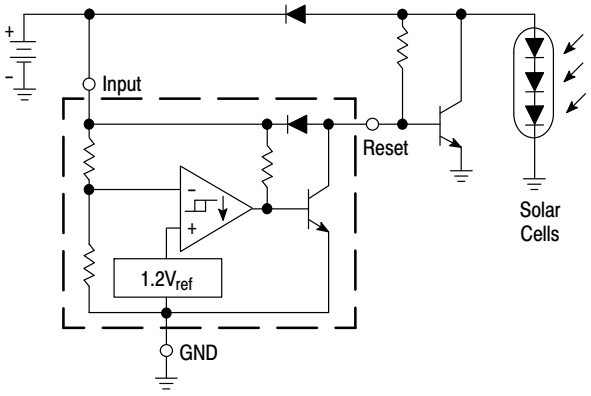
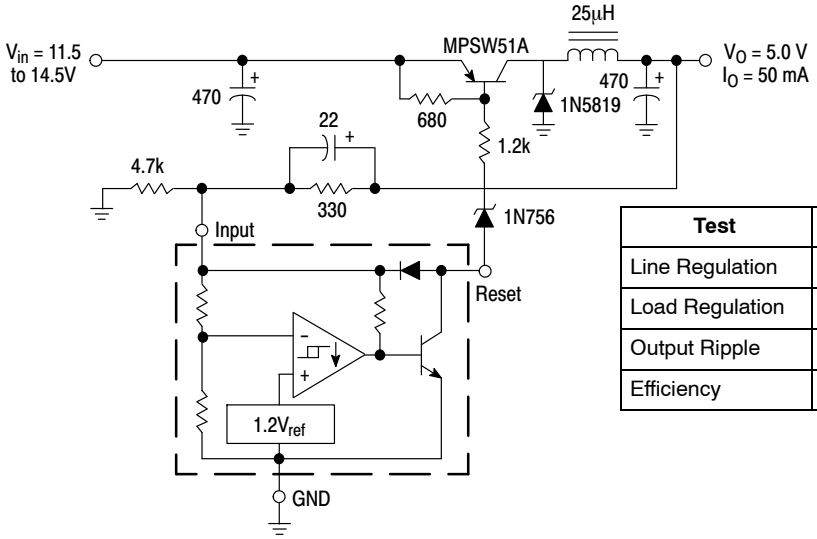
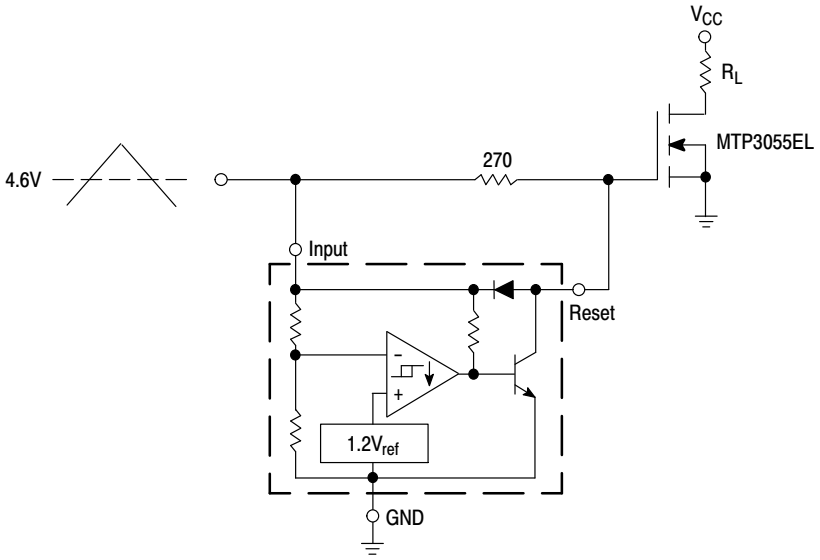


Figure 12. Solar Powered Battery Charger



Test	Conditions	Results
Line Regulation	V_{in} = 11.5 V to 14.5 V, I_O = 50 mA	35 mV
Load Regulation	V_{in} = 12.6 V, I_O = 0 mA to 50 mA	12 mV
Output Ripple	V_{in} = 12.6 V, I_O = 50 mA	60 mVpp
Efficiency	V_{in} = 12.6 V, I_O = 50 mA	77%

Figure 13. Low Power Switching Regulator



Overheating of the logic level power MOSFET due to insufficient gate voltage can be prevented with the above circuit. When the input signal is below the 4.6 V threshold of the MC34064, its output grounds the gate of the L^2 MOSFET.

Figure 14. MOSFET Low Voltage Gate Drive Protection

ORDERING INFORMATION

Device	Operating Temperature Range	Package	Shipping†
MC34064D−5G	T_A = 0°C to +70°C	SOIC−8 (Pb−Free)	98 Units / Rail
MC34064D−5R2G		SOIC−8 (Pb−Free)	2,500 Units/ Tape & Reel
MC34064P−5G		TO−92 (Pb−Free)	2,000 Units / Bag
MC34064P−5RAG		TO−92 (Pb−Free)	2,000 Units / Tape & Reel
MC34064P−5RMG		TO−92 (Pb−Free)	2,000 Units / Ammo Pack
MC34064SN−5T1G		TSOP−5 (Pb−Free)	3,000 Units / Tape & Reel
MC33064D−5G	T_A = −40°C to +85°C	SOIC−8 (Pb−Free)	98 Units / Rail
MC33064D−5R2G		SOIC−8 (Pb−Free)	2,500 Units / Tape & Reel
MC33064P−5G		TO−92 (Pb−Free)	2,000 Units / Bag
MC33064P−5RAG		TO−92 (Pb−Free)	2,000 Units / Tape & Reel
MC33064P−5RPG		TO−92 (Pb−Free)	2,000 Units / Ammo Pack

DISCONTINUED (Note 6)

MC34064DM−5R2G	T_A = 0°C to +70°C	Micro8 (Pb−Free)	4,000 Units / Tape & Reel
MC34064P−5RPG	T_A = 0°C to +70°C	TO−92 (Pb−Free)	2,000 Units / Ammo Pack
MC33064DM−5R2G	T_A = −40°C to +85°C	Micro8 (Pb−Free)	4,000 Units / Tape & Reel
MC33064SN−5T1G	T_A = −40°C to +85°C	TSOP−5 (Pb−Free)	3,000 Units / Tape & Reel
NCV33064D−5R2G*	T_A = −40°C to +125°C	SOIC−8 (Pb−Free)	2,500 Units / Tape & Reel
NCV33064P−5RAG*		TO−92 (Pb−Free)	2,000 Units / Tape & Reel
NCV33064P−5RPG*		TO−92 (Pb−Free)	2,000 Units / Ammo Pack
NCV33064DM−5R2G*		Micro8 (Pb−Free)	4,000 Units / Tape & Reel

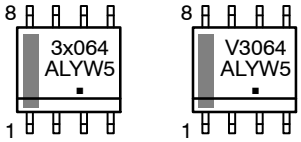
†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

6. **DISCONTINUED:** These devices are not recommended for new design. Please contact your **onsemi** representative for information. The most current information on these devices may be available on www.onsemi.com.

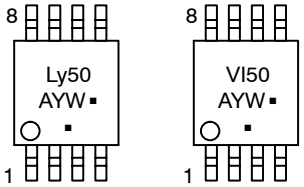
*NCV33064: T_{low} = −40°C, T_{high} = +125°C. Guaranteed by design. NCV prefix is for automotive and other applications requiring site and change control.

MARKING DIAGRAMS

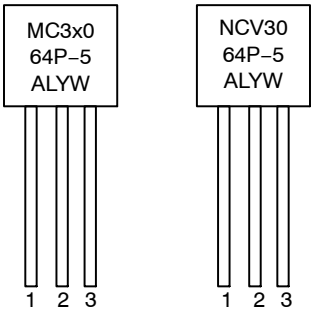
SOIC−8
D SUFFIX
CASE 751



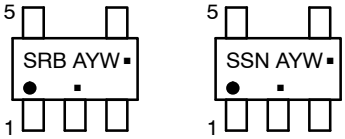
Micro8
DM SUFFIX
CASE 846A



TO−92
P SUFFIX
CASE 029



TSOP−5
SN SUFFIX
CASE 483



MC34064 **MC33064**

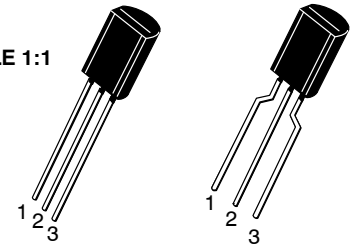
x	=	3 or 4
y	=	C or I
A	=	Assembly Location
L	=	Wafer Lot
Y	=	Year
W	=	Work Week
▪	=	Pb−Free Package

(Note: Microdot may be in either location)

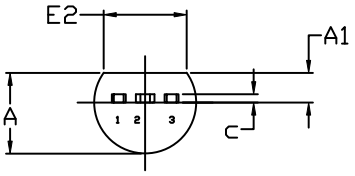
TO−92 (TO−226) 1 WATT
CASE 29−10
ISSUE D

DATE 05 MAR 2021

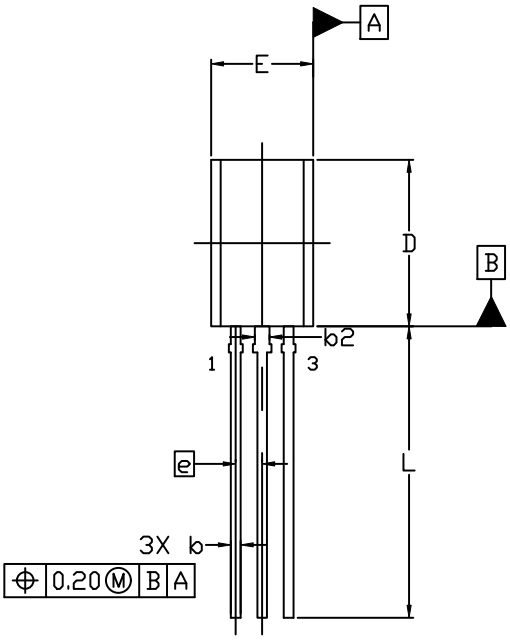
SCALE 1:1



STRAIGHT LEAD



END VIEW



TOP VIEW

NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
2. CONTROLLING DIMENSION: MILLIMETERS
3. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH OR GATE PROTRUSIONS.
4. DIMENSION b AND b2 DOES NOT INCLUDE DAMBAR PROTRUSION. LEAD WIDTH INCLUDING PROTRUSION SHALL NOT EXCEED 0.20. DIMENSION b2 LOCATED ABOVE THE DAMBAR PORTION OF MIDDLE LEAD.

	MILLIMETERS		
DIM	MIN.	NOM.	MAX.
A	3.75	3.90	4.05
A1	1.28	1.43	1.58
b	0.38	0.465	0.55
b2	0.62	0.70	0.78
c	0.35	0.40	0.45
D	7.85	8.00	8.15
E	4.75	4.90	5.05
E2	3.90	---	---
e	1.27 BSC		
L	13.80	14.00	14.20

STYLES AND MARKING ON PAGE 3

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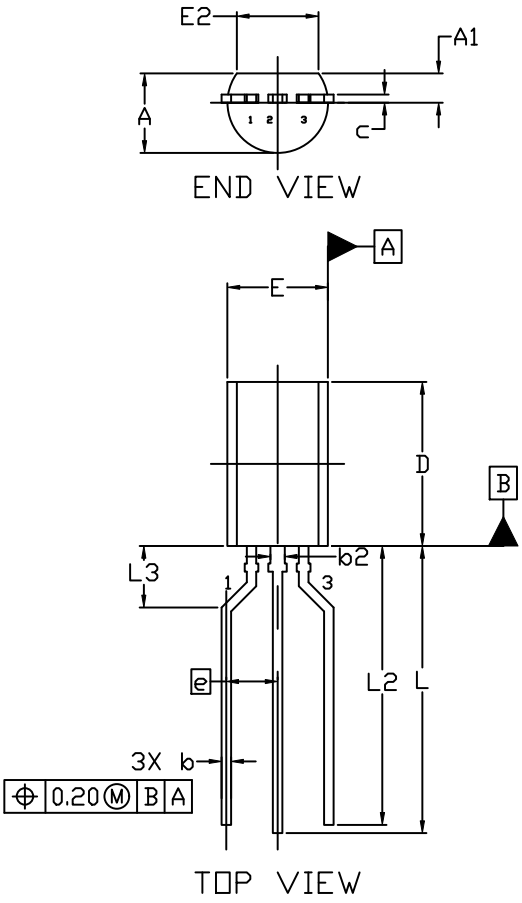
TO−92 (TO−226) 1 WATT
CASE 29−10
ISSUE D

DATE 05 MAR 2021

FORMED LEAD



NOTES:
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	MILLIMETERS		
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A1	1.28	1.43	1.58
b	0.38	0.465	0.55
b2	0.62	0.70	0.78
c	0.35	0.40	0.45
D	7.85	8.00	8.15
E	4.75	4.90	5.05
E2	3.90	---	---
e	2.50 BSC		
L	13.80	14.00	14.20
L2	13.20	13.60	14.00
L3	3.00 REF		

STYLES AND MARKING ON PAGE 3

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TO−92 (TO−226) 1 WATT
CASE 29−10
ISSUE D

DATE 05 MAR 2021

STYLE 1:
PIN 1. EMITTER
2. BASE
3. COLLECTOR

STYLE 2:
PIN 1. BASE
2. EMITTER
3. COLLECTOR

STYLE 3:
PIN 1. ANODE
2. ANODE
3. CATHODE

STYLE 4:
PIN 1. CATHODE
2. CATHODE
3. ANODE

STYLE 5:
PIN 1. DRAIN
2. SOURCE
3. GATE

STYLE 6:
PIN 1. GATE
2. SOURCE & SUBSTRATE
3. DRAIN

STYLE 7:
PIN 1. SOURCE
2. DRAIN
3. GATE

STYLE 8:
PIN 1. DRAIN
2. GATE
3. SOURCE & SUBSTRATE

STYLE 9:
PIN 1. BASE 1
2. EMITTER
3. BASE 2

STYLE 10:
PIN 1. CATHODE
2. GATE
3. ANODE

STYLE 11:
PIN 1. ANODE
2. CATHODE & ANODE
3. CATHODE

STYLE 12:
PIN 1. MAIN TERMINAL 1
2. GATE
3. MAIN TERMINAL 2

STYLE 13:
PIN 1. ANODE 1
2. GATE
3. CATHODE 2

STYLE 14:
PIN 1. EMITTER
2. COLLECTOR
3. BASE

STYLE 15:
PIN 1. ANODE 1
2. CATHODE
3. ANODE 2

STYLE 16:
PIN 1. ANODE
2. GATE
3. CATHODE

STYLE 17:
PIN 1. COLLECTOR
2. BASE
3. EMITTER

STYLE 18:
PIN 1. ANODE
2. CATHODE
3. NOT CONNECTED

STYLE 19:
PIN 1. GATE
2. ANODE
3. CATHODE

STYLE 20:
PIN 1. NOT CONNECTED
2. CATHODE
3. ANODE

STYLE 21:
PIN 1. COLLECTOR
2. EMITTER
3. BASE

STYLE 22:
PIN 1. SOURCE
2. GATE
3. DRAIN

STYLE 23:
PIN 1. GATE
2. SOURCE
3. DRAIN

STYLE 24:
PIN 1. EMITTER
2. COLLECTOR/ANODE
3. CATHODE

STYLE 25:
PIN 1. MT 1
2. GATE
3. MT 2

STYLE 26:
PIN 1. V_{CC}
2. GROUND 2
3. OUTPUT

STYLE 27:
PIN 1. MT
2. SUBSTRATE
3. MT

STYLE 28:
PIN 1. CATHODE
2. ANODE
3. GATE

STYLE 29:
PIN 1. NOT CONNECTED
2. ANODE
3. CATHODE

STYLE 30:
PIN 1. DRAIN
2. GATE
3. SOURCE

STYLE 31:
PIN 1. GATE
2. DRAIN
3. SOURCE

STYLE 32:
PIN 1. BASE
2. COLLECTOR
3. EMITTER

STYLE 33:
PIN 1. RETURN
2. INPUT
3. OUTPUT

STYLE 34:
PIN 1. INPUT
2. GROUND
3. LOGIC

STYLE 35:
PIN 1. GATE
2. COLLECTOR
3. EMITTER

GENERIC MARKING DIAGRAM*

XXXX = Specific Device Code
A = Assembly Location
L = Wafer Lot
Y = Year
W = Work Week
▪ = Pb−Free Package

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “▪”, may or may not be present. Some products may not follow the Generic Marking.

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DESCRIPTION:	**TO−92 (TO−226) 1 WATT**		**PAGE 3 OF 3**

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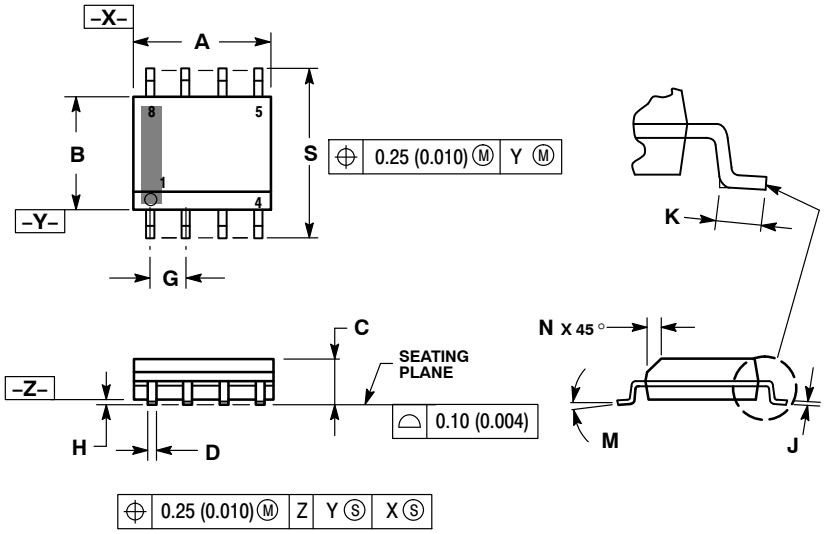
SCALE 1:1

SOIC−8 NB
CASE 751−07
ISSUE AK

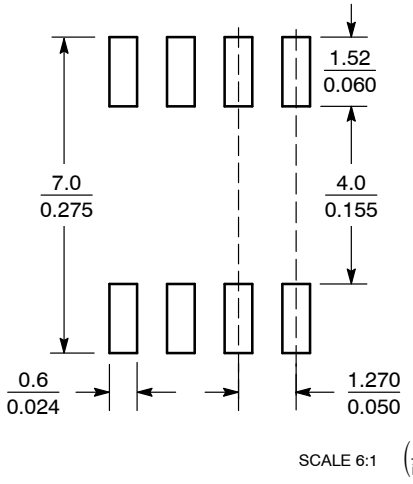
DATE 16 FEB 2011



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A AND B DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. 751−01 THRU 751−06 ARE OBSOLETE. NEW STANDARD IS 751−07.

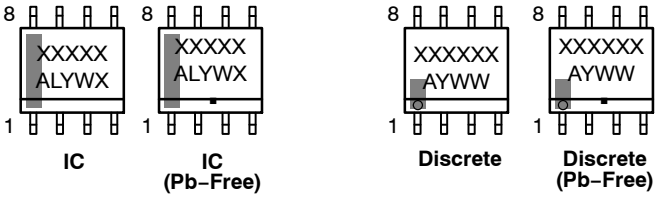
	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	4.80	5.00	0.189	0.197
B	3.80	4.00	0.150	0.157
C	1.35	1.75	0.053	0.069
D	0.33	0.51	0.013	0.020
G	1.27 BSC		0.050 BSC	
H	0.10	0.25	0.004	0.010
J	0.19	0.25	0.007	0.010
K	0.40	1.27	0.016	0.050
M	0°	8°	0°	8°
N	0.25	0.50	0.010	0.020
S	5.80	6.20	0.228	0.244

SOLDERING FOOTPRINT*



*For additional information on our Pb−Free strategy and soldering details, please download the **onsemi** Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

GENERIC MARKING DIAGRAM*



XXXXX = Specific Device Code
A = Assembly Location
L = Wafer Lot
Y = Year
W = Work Week
▪ = Pb−Free Package

XXXXXX = Specific Device Code
A = Assembly Location
Y = Year
WW = Work Week
▪ = Pb−Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

STYLES ON PAGE 2

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DESCRIPTION:	**SOIC−8 NB**		**PAGE 1 OF 2**

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SOIC−8 NB
CASE 751−07
ISSUE AK

DATE 16 FEB 2011

STYLE 1:
PIN 1. EMITTER
2. COLLECTOR
3. COLLECTOR
4. EMITTER
5. EMITTER
6. BASE
7. BASE
8. EMITTER

STYLE 2:
PIN 1. COLLECTOR, DIE, #1
2. COLLECTOR, #1
3. COLLECTOR, #2
4. COLLECTOR, #2
5. BASE, #2
6. EMITTER, #2
7. BASE, #1
8. EMITTER, #1

STYLE 3:
PIN 1. DRAIN, DIE #1
2. DRAIN, #1
3. DRAIN, #2
4. DRAIN, #2
5. GATE, #2
6. SOURCE, #2
7. GATE, #1
8. SOURCE, #1

STYLE 4:
PIN 1. ANODE
2. ANODE
3. ANODE
4. ANODE
5. ANODE
6. ANODE
7. ANODE
8. COMMON CATHODE

STYLE 5:
PIN 1. DRAIN
2. DRAIN
3. DRAIN
4. DRAIN
5. GATE
6. GATE
7. SOURCE
8. SOURCE

STYLE 6:
PIN 1. SOURCE
2. DRAIN
3. DRAIN
4. SOURCE
5. SOURCE
6. GATE
7. GATE
8. SOURCE

STYLE 7:
PIN 1. INPUT
2. EXTERNAL BYPASS
3. THIRD STAGE SOURCE
4. GROUND
5. DRAIN
6. GATE 3
7. SECOND STAGE Vd
8. FIRST STAGE Vd

STYLE 8:
PIN 1. COLLECTOR, DIE #1
2. BASE, #1
3. BASE, #2
4. COLLECTOR, #2
5. COLLECTOR, #2
6. EMITTER, #2
7. EMITTER, #1
8. COLLECTOR, #1

STYLE 9:
PIN 1. EMITTER, COMMON
2. COLLECTOR, DIE #1
3. COLLECTOR, DIE #2
4. EMITTER, COMMON
5. EMITTER, COMMON
6. BASE, DIE #2
7. BASE, DIE #1
8. EMITTER, COMMON

STYLE 10:
PIN 1. GROUND
2. BIAS 1
3. OUTPUT
4. GROUND
5. GROUND
6. BIAS 2
7. INPUT
8. GROUND

STYLE 11:
PIN 1. SOURCE 1
2. GATE 1
3. SOURCE 2
4. GATE 2
5. DRAIN 2
6. DRAIN 2
7. DRAIN 1
8. DRAIN 1

STYLE 12:
PIN 1. SOURCE
2. SOURCE
3. SOURCE
4. GATE
5. DRAIN
6. DRAIN
7. DRAIN
8. DRAIN

STYLE 13:
PIN 1. N.C.
2. SOURCE
3. SOURCE
4. GATE
5. DRAIN
6. DRAIN
7. DRAIN
8. DRAIN

STYLE 14:
PIN 1. N−SOURCE
2. N−GATE
3. P−SOURCE
4. P−GATE
5. P−DRAIN
6. P−DRAIN
7. N−DRAIN
8. N−DRAIN

STYLE 15:
PIN 1. ANODE 1
2. ANODE 1
3. ANODE 1
4. ANODE 1
5. CATHODE, COMMON
6. CATHODE, COMMON
7. CATHODE, COMMON
8. CATHODE, COMMON

STYLE 16:
PIN 1. EMITTER, DIE #1
2. BASE, DIE #1
3. EMITTER, DIE #2
4. BASE, DIE #2
5. COLLECTOR, DIE #2
6. COLLECTOR, DIE #2
7. COLLECTOR, DIE #1
8. COLLECTOR, DIE #1

STYLE 17:
PIN 1. VCC
2. V2OUT
3. V1OUT
4. TXE
5. RXE
6. VEE
7. GND
8. ACC

STYLE 18:
PIN 1. ANODE
2. ANODE
3. SOURCE
4. GATE
5. DRAIN
6. DRAIN
7. CATHODE
8. CATHODE

STYLE 19:
PIN 1. SOURCE 1
2. GATE 1
3. SOURCE 2
4. GATE 2
5. DRAIN 2
6. MIRROR 2
7. DRAIN 1
8. MIRROR 1

STYLE 20:
PIN 1. SOURCE (N)
2. GATE (N)
3. SOURCE (P)
4. GATE (P)
5. DRAIN
6. DRAIN
7. DRAIN
8. DRAIN

STYLE 21:
PIN 1. CATHODE 1
2. CATHODE 2
3. CATHODE 3
4. CATHODE 4
5. CATHODE 5
6. COMMON ANODE
7. COMMON ANODE
8. CATHODE 6

STYLE 22:
PIN 1. I/O LINE 1
2. COMMON CATHODE/VCC
3. COMMON CATHODE/VCC
4. I/O LINE 3
5. COMMON ANODE/GND
6. I/O LINE 4
7. I/O LINE 5
8. COMMON ANODE/GND

STYLE 23:
PIN 1. LINE 1 IN
2. COMMON ANODE/GND
3. COMMON ANODE/GND
4. LINE 2 IN
5. LINE 2 OUT
6. COMMON ANODE/GND
7. COMMON ANODE/GND
8. LINE 1 OUT

STYLE 24:
PIN 1. BASE
2. EMITTER
3. COLLECTOR/ANODE
4. COLLECTOR/ANODE
5. CATHODE
6. CATHODE
7. COLLECTOR/ANODE
8. COLLECTOR/ANODE

STYLE 25:
PIN 1. VIN
2. N/C
3. REXT
4. GND
5. IOUT
6. IOUT
7. IOUT
8. IOUT

STYLE 26:
PIN 1. GND
2. dv/dt
3. ENABLE
4. ILIMIT
5. SOURCE
6. SOURCE
7. SOURCE
8. VCC

STYLE 27:
PIN 1. ILIMIT
2. OVLO
3. UVLO
4. INPUT+
5. SOURCE
6. SOURCE
7. SOURCE
8. DRAIN

STYLE 28:
PIN 1. SW_TO_GND
2. DASIC_OFF
3. DASIC_SW_DET
4. GND
5. V_MON
6. VBULK
7. VBULK
8. VIN

STYLE 29:
PIN 1. BASE, DIE #1
2. EMITTER, #1
3. BASE, #2
4. EMITTER, #2
5. COLLECTOR, #2
6. COLLECTOR, #2
7. COLLECTOR, #1
8. COLLECTOR, #1

STYLE 30:
PIN 1. DRAIN 1
2. DRAIN 1
3. GATE 2
4. SOURCE 2
5. SOURCE 1/DRAIN 2
6. SOURCE 1/DRAIN 2
7. SOURCE 1/DRAIN 2
8. GATE 1

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DESCRIPTION:	**SOIC−8 NB**		**PAGE 2 OF 2**

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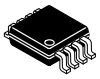
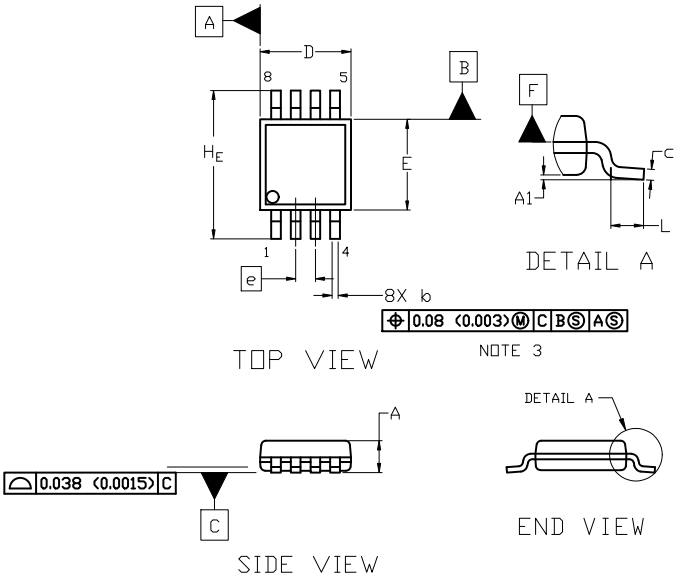


SCALE 2:1

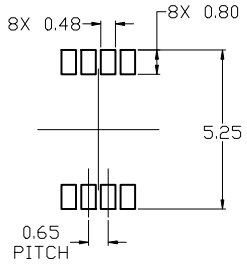
Micro8
CASE 846A−02
ISSUE K

DATE 16 JUL 2020



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
2. CONTROLLING DIMENSION: MILLIMETERS
3. DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.10 mm IN EXCESS OF MAXIMUM MATERIAL CONDITION.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSION OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.15 mm PER SIDE. DIMENSION E DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 mm PER SIDE. DIMENSIONS D AND E ARE DETERMINED AT DATUM F.
5. DATUMS A AND B ARE TO BE DETERMINED AT DATUM F.
6. A1 IS DEFINED AS THE VERTICAL DISTANCE FROM THE SEATING PLANE TO THE LOWEST POINT ON THE PACKAGE BODY.

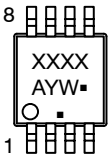


RECOMMENDED
MOUNTING FOOTPRINT

For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	---	---	1.10
A1	0.05	0.08	0.15
b	0.25	0.33	0.40
c	0.13	0.18	0.23
D	2.90	3.00	3.10
E	2.90	3.00	3.10
e	0.65 BSC		
H_E	4.75	4.90	5.05
L	0.40	0.55	0.70

GENERIC MARKING DIAGRAM*



XXXX = Specific Device Code
A = Assembly Location
Y = Year
W = Work Week
▪ = Pb−Free Package

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “▪”, may or may not be present. Some products may not follow the Generic Marking.

STYLE 1:
PIN 1. SOURCE
2. SOURCE
3. SOURCE
4. GATE
5. DRAIN
6. DRAIN
7. DRAIN
8. DRAIN

STYLE 2:
PIN 1. SOURCE 1
2. GATE 1
3. SOURCE 2
4. GATE 2
5. DRAIN 2
6. DRAIN 2
7. DRAIN 1
8. DRAIN 1

STYLE 3:
PIN 1. N-SOURCE
2. N-GATE
3. P-SOURCE
4. P-GATE
5. P-DRAIN
6. P-DRAIN
7. N-DRAIN
8. N-DRAIN

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DESCRIPTION:	**MICRO8**	**PAGE 1 OF 1**

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